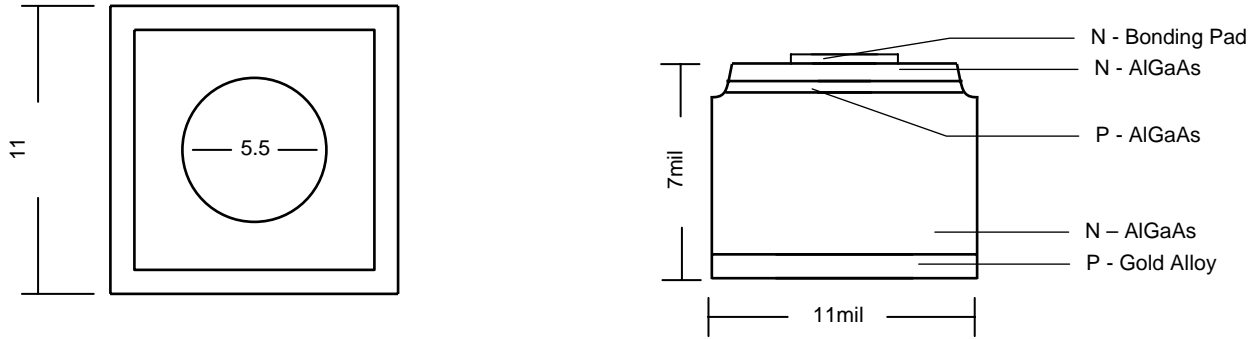


TCM910-10

❖ Outline Dimensions:



❖ Physical Structure:

Chip dimensions		Chip size	11 mil x 11 mil	280 μm x 280 μm
		Thickness	7 mil	180 μm
		Bonding pad	5.5 mil	140 μm
Electrode	Top	N (cathode)	Gold alloy	
	Backside	P (anode)	Gold alloy	

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	-	1.40	1.60	V
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5	-	-	V
Peak Wavelength	λ_P	$I_F = 20\text{mA}$	900	910	920	nm
Spectral Bandwidth	$\Delta\lambda$	$I_F = 20\text{mA}$	-	80	-	nm
Radiant Flux	P_O	$I_F = 20\text{mA}$	0.7	1.2	-	mW